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INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

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Application Number	09/943134
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Ho, Tu-Tu

Sheet 1 of 3

Attorney Docket No: 1303.020US1

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**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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